

G8551S

PNP EPITAXIAL SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

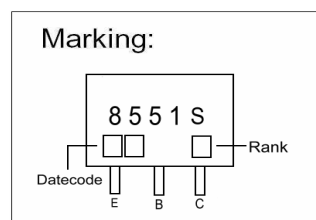
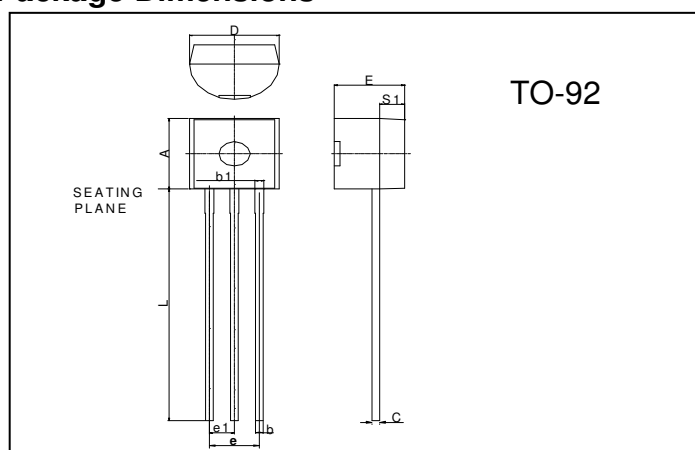
Description

The G8551 is a low voltage high current small signal PNP transistor, designed for Class B push-pull audio amplifier for portable radio and general purpose applications.

Features

- *Collector current up to 700mA
- *Collector –Emitter voltage up to 20V
- *Complimentary to G8051S

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter		Ratings	Unit
Collector to Base Voltage	VCBO	-25	V
Collector to Emitter Voltage	VCEO	-20	V
Emitter to Base Voltage	VEBO	-5	V
Collect Current(DC)	Ic	-0.7	A
Junction Temperature	Tj	+150	°C
Storage Temperature Range	TSTG	-55 ~ +150	°C
Total Power Dissipation	PD	625	mW

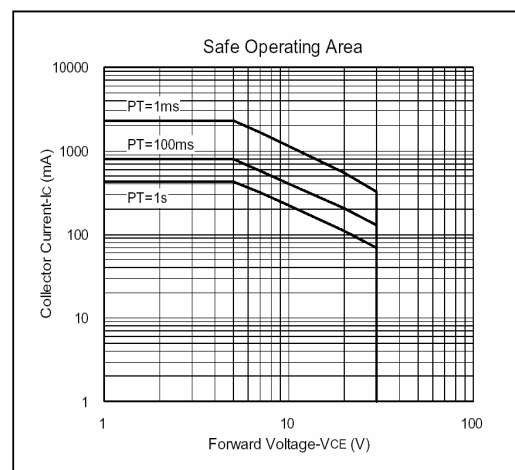
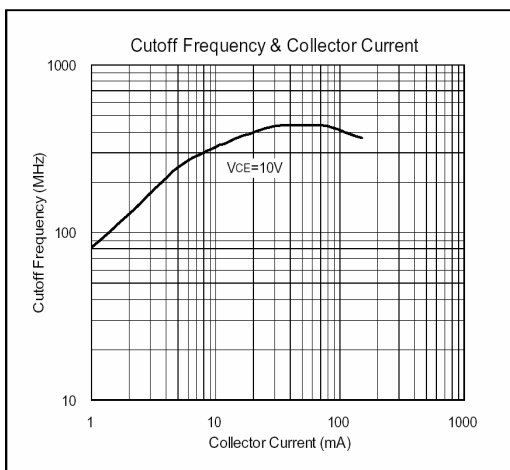
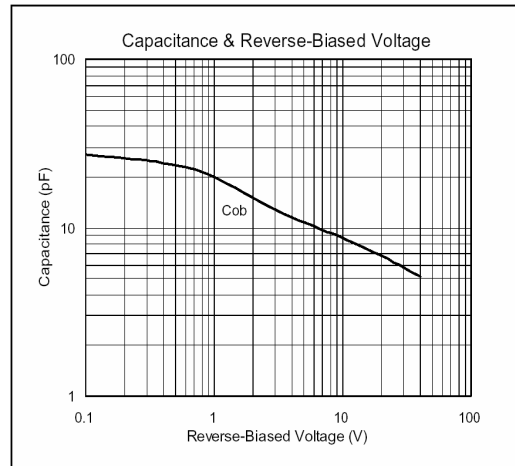
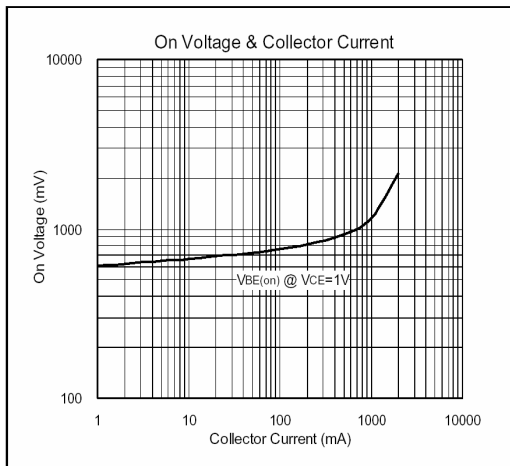
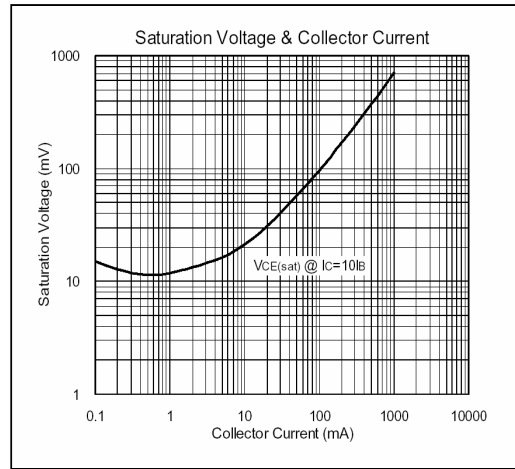
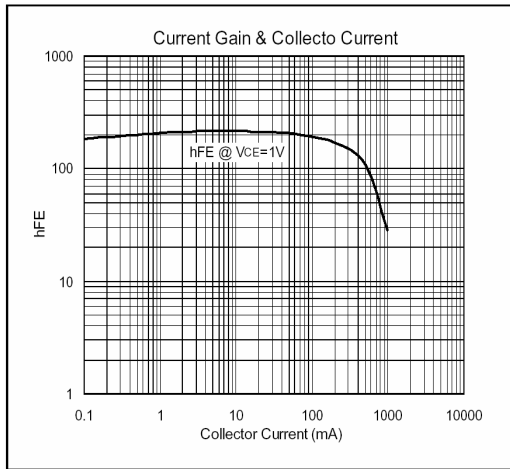
Electrical Characteristics (Ta = 25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-25	-	-	V	Ic=-10uA, IE=0
BVCEO	-20	-	-	V	Ic=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-10uA, Ic=0
ICBO	-	-	-1	uA	VCB=-20V, IE=0
hFE1	100	-	500		VCE=-1V, Ic=-150mA
hFE2	-	100	-		VCE=-1V, Ic=-500mA
VCE(sat)	-	-	-0.5	V	Ic=-500mA, IB=-50mA
VBE(on)	-	-	-1	V	VCE=-1V, Ic=-150mA
VBE	-	-	-1.0	V	VCE=-1V, Ic=-10mA
fT	150	-	-	MHz	VCE=-10V, Ic=-20Ma, f=100MHz
Cob	-	10	-	pF	VCB=-10V, IE=0A, f=1MHz

Classification Of hFE1

Rank	C	D	E
Range	100-180	160-300	280-500

Characteristics Curve



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